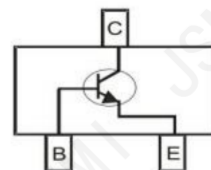


■ Features 特点
NPN General Purpose 通用

Absolute Maximum Ratings 最大额定值

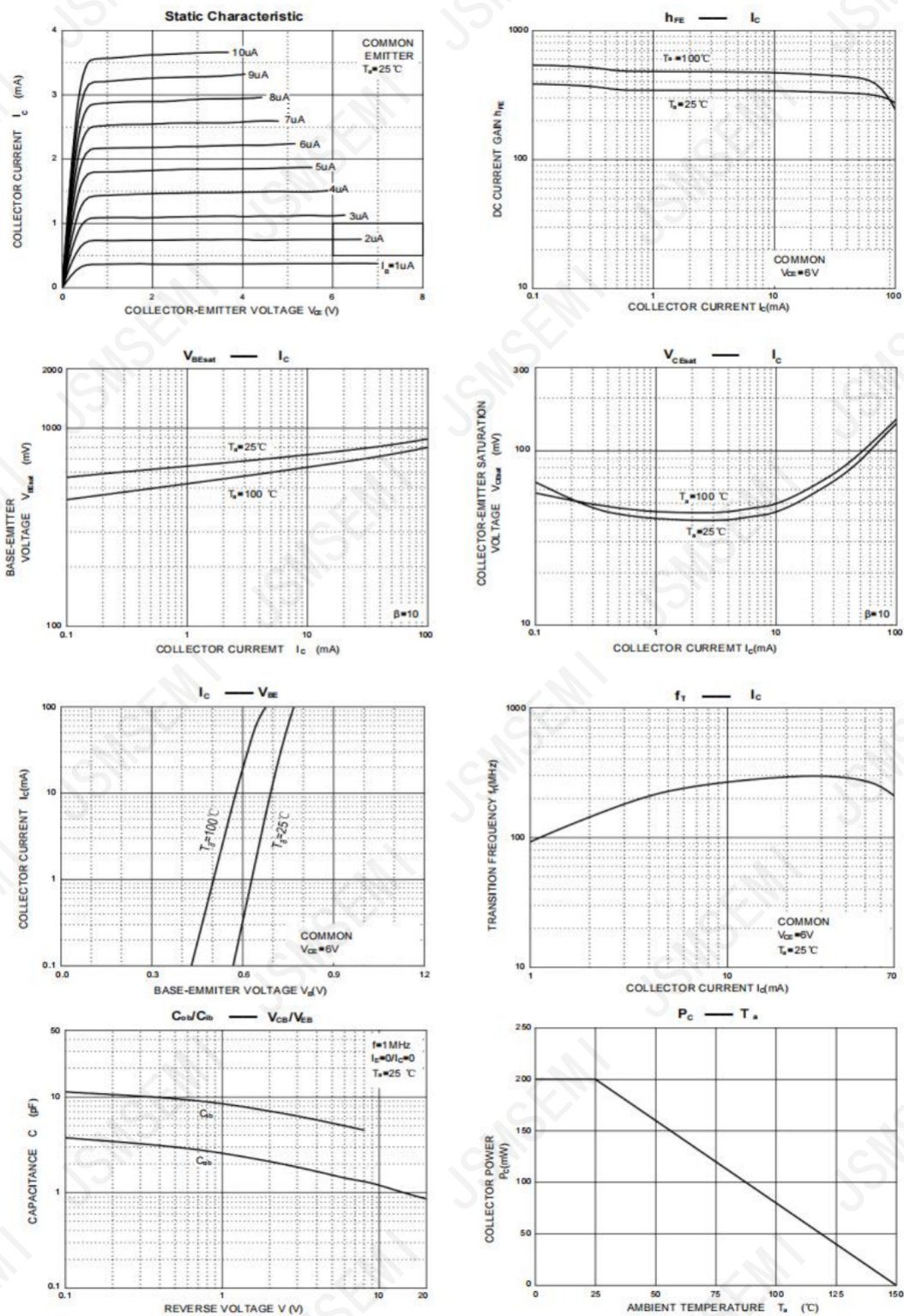
Characteristic 特性参数	Symbol 符号	BC846C	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	80	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	65	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	6	V
Collector Current 集电极电流	I_C	100	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}\text{C})$	200	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	625	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}\text{C}$	

Electrical Characteristics 电特性

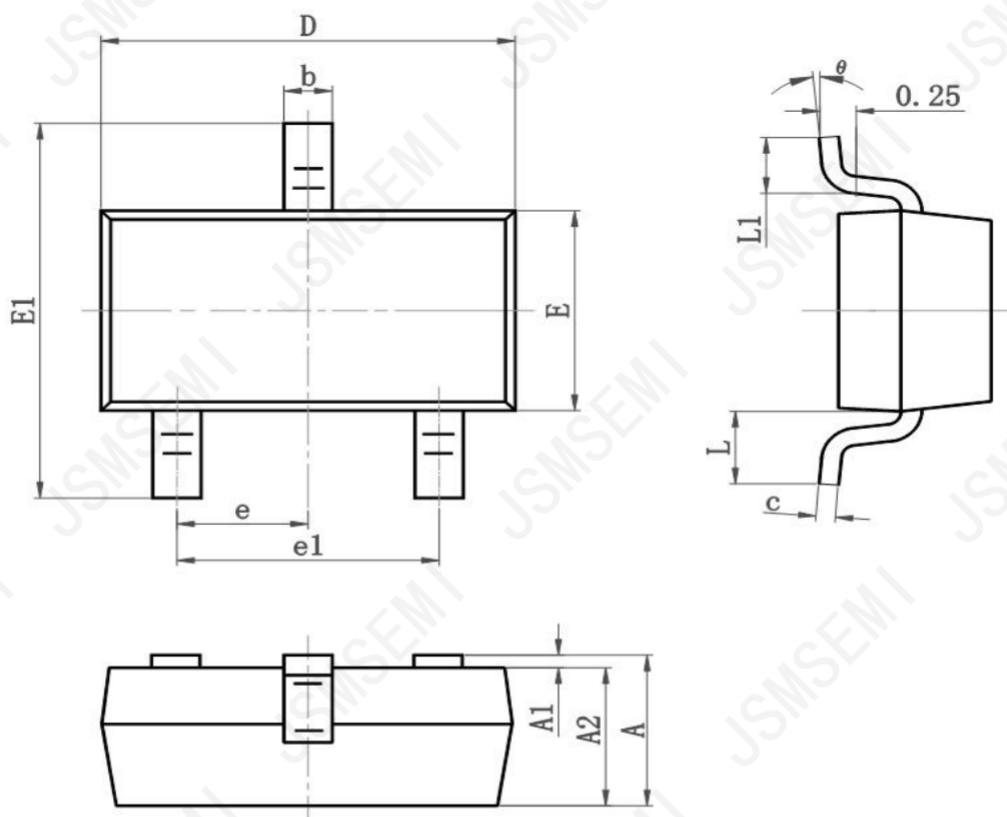
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压 ($I_C=10\mu\text{A}$, $I_E=0$)	BV_{CBO}	80	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压 ($I_C=10\text{mA}$, $I_B=0$)	BV_{CEO}	65	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压 ($I_E=10\mu\text{A}$, $I_C=0$)	BV_{EBO}	5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流 ($V_{CB}=70\text{V}$, $I_E=0$)	I_{CBO}	—	—	100	nA
Emitter-Base Leakage Current 发射极基极漏电流 ($V_{EB}=5\text{V}$, $I_C=0$)	I_{EBO}	—	—	100	nA
DC Current Gain 直流电流增益 ($V_{CE}=5\text{V}$, $I_C=2\text{mA}$)	H_{FE}	420	520	800	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ($I_C=100\text{mA}$, $I_B=5\text{mA}$)	$V_{CE(sat)}$	—	—	0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 ($I_C=100\text{mA}$, $I_B=5\text{mA}$)	$V_{BE(sat)}$	—	—	1.1	V
Transition Frequency 特征频率 ($V_{CE}=5\text{V}$, $I_C=10\text{mA}$)	f_T	100	—	—	MHz
Output Capacitance 输出电容 ($V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$)	C_{ob}	—	4.5	—	pF

Typical Characteristic Curve 典型特性曲线



Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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